

R-C Thermal Model Parameters

DESCRIPTION

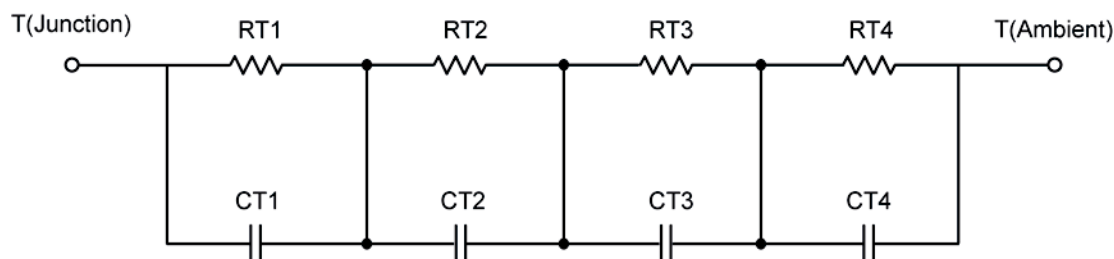
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	41.6492	N/A	14.6446
RT2	44.6228	N/A	37.4034
RT3	18.0823	N/A	30.1142
RT4	45.6457	N/A	7.8378
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	11.4251 m	N/A	4.3719 m
CT2	25.4128 m	N/A	29.9032 m
CT3	714.9994 u	N/A	12.8329 m
CT4	1.3996	N/A	236.4579 u

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	19.1973	N/A	4.5563
RF2	34.8418	N/A	9.4167
RF3	48.4147	N/A	31.0150
RF4	47.5462	N/A	45.0120
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	623.8645 μ	N/A	79.6667 μ
CF2	5.7263 m	N/A	847.8969 μ
CF3	5.6466 m	N/A	2.6649 m
CF4	1.2573	N/A	14.3545 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

